ABSTRACT

SILICON WAFER AND PRODUCTION METHOD THEREFOR

A silicon wafer including BMD with a diagonal length of from 10 nm to 50 nm, wherein, a density of the BMD which exists at a position of a depth of equal to or deeper than 50 μm from the surface of said silicon wafer is equal to or higher than $1\times10^{11}/cm^3$, and a ratio of the {111} plane in total planes surrounding BMD, as morphology of the BMD, is equal to or lower than 0.3.

Figure 8